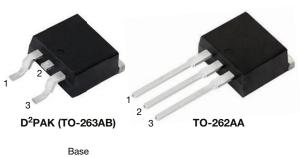
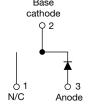
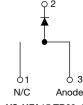
### VS-HFA15TB60S-M3, VS-HFA15TB60-1-M3

Vishay Semiconductors

# HEXFRED®, Ultrafast Soft Recovery Diode, 15 A







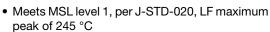
VS-HFA15 TB60S-M3

VS-HFA15 TB60-1-M3

| PRIMARY CHARACTERISTICS          |   |  |  |  |  |  |
|----------------------------------|---|--|--|--|--|--|
| I <sub>F(AV)</sub>               | 15 A                                    |  |  |  |  |  |
| V <sub>R</sub>                   | 600 V                                   |  |  |  |  |  |
| V <sub>F</sub> at I <sub>F</sub> | 1.2 V                                   |  |  |  |  |  |
| t <sub>rr</sub> (typ.)           | 23 ns                                   |  |  |  |  |  |
| T <sub>J</sub> max.              | 150 °C                                  |  |  |  |  |  |
| Package                          | D <sup>2</sup> PAK (TO-263AB), TO-262AA |  |  |  |  |  |
| Circuit configuration            | Single                                  |  |  |  |  |  |

### **FEATURES**

- Ultrafast and ultrasoft recovery
- Very low I<sub>RRM</sub> and Q<sub>rr</sub>





- Designed and qualified for industrial level
- Material categorization: for definitions of compliance please see <a href="https://www.vishay.com/doc?99912"><u>www.vishay.com/doc?99912</u></a>

#### **BENEFITS**

- Reduced RFI and EMI
- Reduced power loss in diode and switching transistor
- Higher frequency operation
- · Reduced snubbing
- · Reduced parts count

#### **DESCRIPTION**

VS-HFA15TB60S, VS-HFA15TB60-1 is a state of the art ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 600 V and 15 A continuous current, the VS-HFA15TB60S. VS-HFA15TB60-1 is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I<sub>RRM</sub>) and does not exhibit any tendency to "snap-off" during the tb portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and sizes. The HEXFRED VS-HFA15TB60S, VS-HFA15TB60-1 is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

| ABSOLUTE MAXIMUM RATINGS                         |                                   |                         |             |       |  |  |  |
|--|-----------------------------------|-------------------------|-------------|-------|--|--|--|
| PARAMETER  | SYMBOL                            | TEST CONDITIONS         | VALUES      | UNITS |  |  |  |
| Cathode to anode voltage                         | V <sub>R</sub>                    |                         | 600         | V     |  |  |  |
| Maximum continuous forward current               | I <sub>F</sub>                    | T <sub>C</sub> = 100 °C | 15          |       |  |  |  |
| Single pulse forward current                     | I <sub>FSM</sub>                  |                         | 150         | Α     |  |  |  |
| Maximum repetitive forward current               | I <sub>FRM</sub>                  |                         | 60          |       |  |  |  |
| Maximum naucas discination                       | ם                                 | T <sub>C</sub> = 25 °C  | 74          | W     |  |  |  |
| Maximum power dissipation                        | $P_D$                             | T <sub>C</sub> = 100 °C | 29          | VV    |  |  |  |
| Operating junction and storage temperature range | T <sub>J</sub> , T <sub>Stg</sub> |                         | -55 to +150 | °C    |  |  |  |



# VS-HFA15TB60S-M3, VS-HFA15TB60-1-M3

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| <b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified) |                 |  |                 |     |     |      |       |
|--|-----------------|--|-----------------|-----|-----|------|-------|
| PARAMETER  | SYMBOL          | TEST CONDITIONS  | TEST CONDITIONS |     |     |      | UNITS |
| Cathode to anode breakdown voltage   | $V_{BR}$        | I <sub>R</sub> = 100 μA  |                 | 600 | -   | -    |       |
|  |                 | I <sub>F</sub> = 15 A  |                 | -   | 1.3 | 1.7  | V     |
| Maximum forward voltage  | $V_{FM}$        | I <sub>F</sub> = 30 A  | See fig. 1      | -   | 1.5 | 2.0  |       |
|  |                 | I <sub>F</sub> = 15 A, T <sub>J</sub> = 125 °C                         |                 | -   | 1.2 | 1.6  |       |
| Maximum reverse  |                 | $V_R = V_R$ rated  | See fig. 2      | -   | 1.0 | 10   |       |
| leakage current  | I <sub>RM</sub> | $T_J = 125  ^{\circ}\text{C},  V_R = 0.8  \text{x}  V_R  \text{rated}$ | See lig. 2      | -   | 400 | 1000 | μΑ    |
| Junction capacitance   | C <sub>T</sub>  | V <sub>R</sub> = 200 V   | See fig. 3      | -   | 25  | 50   | pF    |
| Series inductance  | L <sub>S</sub>  | Measured lead to lead 5 mm from pa                                     | ackage body     | -   | 8.0 | -    | nH    |

| DYNAMIC RECOVERY                            | CHARACT                   | TERISTICS (T <sub>J</sub> = 25                 | °C unless otherwise  | specifie | d)   |      |             |
|---|---------------------------|--|--|----------|------|------|-------------|
| PARAMETER                                   | SYMBOL                    | TEST COM                                       | NDITIONS   | MIN.     | TYP. | MAX. | UNITS       |
| D   | t <sub>rr</sub>           | $I_F = 1.0 \text{ A}, dI_F/dt = 200 \text{ A}$ | 4/μs, V <sub>R</sub> = 30 V  | -        | 23   | -    |             |
| Reverse recovery time See fig. 5            | t <sub>rr1</sub>          | T <sub>J</sub> = 25 °C                         |  | -        | 50   | 60   | ns          |
|   | t <sub>rr2</sub>          | T <sub>J</sub> = 125 °C                        |  | -        | 105  | 120  |             |
| Peak recovery current                       | I <sub>RRM1</sub>         | T <sub>J</sub> = 25 °C                         | $I_F = 15 \text{ A}$<br>$dI_F/dt = 200 \text{ A/}\mu\text{s}$<br>$V_R = 200 \text{ V}$ | -        | 4.5  | 6.0  | - A<br>- nC |
| See fig. 6                                  | I <sub>RRM2</sub>         | T <sub>J</sub> = 125 °C                        |  | -        | 6.5  | 10   |             |
| Reverse recovery charge                     | Q <sub>rr1</sub>          | T <sub>J</sub> = 25 °C                         |  | -        | 84   | 180  |             |
| See fig. 7                                  | Q <sub>rr2</sub>          | T <sub>J</sub> = 125 °C                        |  | -        | 241  | 600  | 110         |
| Peak rate of fall of recovery               | dI <sub>(rec)M</sub> /dt1 | T <sub>J</sub> = 25 °C                         |  | -        | 188  | -    |             |
| current during t <sub>b</sub><br>See fig. 8 | dI <sub>(rec)M</sub> /dt2 | T <sub>J</sub> = 125 °C                        |  | -        | 160  | -    | A/μs        |

| THERMAL - MECHANICAL SPECIFICATIONS     |                   |   |      |             |       |       |  |
|---|-------------------|---|------|-------------|-------|-------|--|
| PARAMETER                               | SYMBOL            | TEST CONDITIONS                             | MIN. | TYP.        | MAX.  | UNITS |  |
| Lead temperature                        | T <sub>lead</sub> | 0.063" from case (1.6 mm) for 10 s          | -    | -           | 300   | °C    |  |
| Thermal resistance, junction-to-case    | R <sub>thJC</sub> |   | -    | -           | 1.7   |       |  |
| Thermal resistance, junction-to-ambient | R <sub>thJA</sub> | Typical socket mount                        | -    | -           | 80    | K/W   |  |
| Thermal resistance, case-to-heatsink    | R <sub>thCS</sub> | Mounting surface, flat, smooth, and greased | -    | 0.5         | -     |       |  |
| Weight                                  |                   |   | -    | 2.0         | -     | g     |  |
| vveigni                                 |                   |   | -    | 0.07        | -     | oz.   |  |
| Marking dayioo                          |                   | Case style D <sup>2</sup> PAK (TO-263AB)    |      | HFA15       | TB60S |       |  |
| Marking device                          |                   | Case style TO-262AA                         |      | HFA15TB60-1 |       |       |  |

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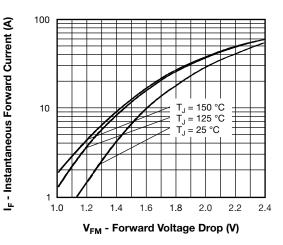


Fig. 1 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current

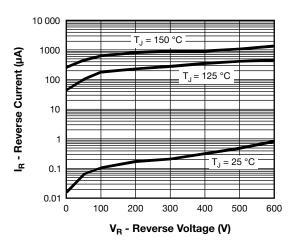


Fig. 2 - Typical Reverse Current vs. Reverse Voltage

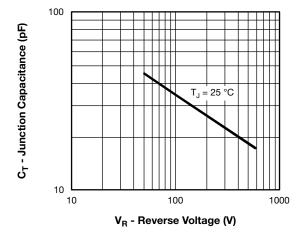


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

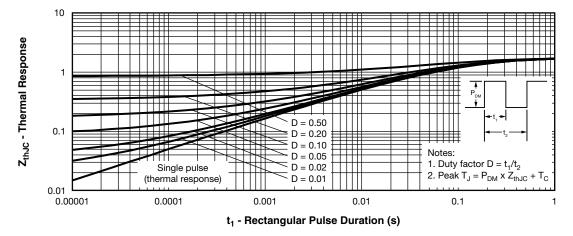


Fig. 4 - Maximum Thermal Impedance Z<sub>thJC</sub> Characteristics

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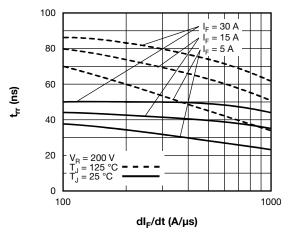


Fig. 5 - Typical Reverse Recovery Time vs. dl<sub>F</sub>/dt

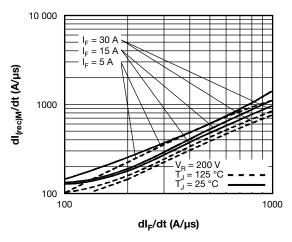


Fig. 8 - Typical  $dI_{(rec)M}/dt$  vs.  $dI_F/dt$ 

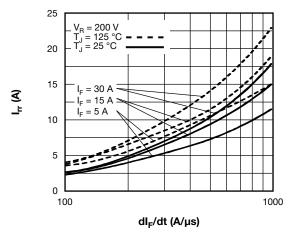


Fig. 6 - Typical Recovery Current vs. dl<sub>F</sub>/dt

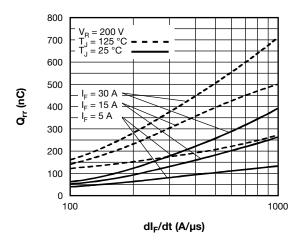
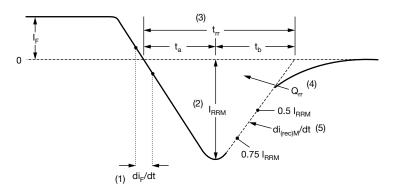


Fig. 7 - Typical Stored Charge vs.  $dI_F/dt$ 

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- (1) di<sub>F</sub>/dt rate of change of current through zero crossing
- (2)  $I_{RRM}$  peak reverse recovery current
- (3)  $\rm t_{rr}$  reverse recovery time measured from zero crossing point of negative going  $\rm I_{r}$  to point where a line passing through 0.75  $\rm I_{RRM}$  and 0.50  $\rm I_{RRM}$  extrapolated to zero current.
- (4)  $\mathbf{Q}_{\rm rr}$  area under curve defined by  $\mathbf{t}_{\rm rr}$  and  $\mathbf{I}_{\rm RRM}$

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5)  $di_{(rec)M}/dt$  - peak rate of change of current during  $t_b$  portion of  $t_{rr}$ 

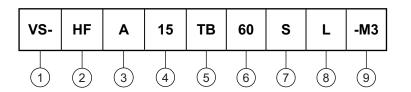
Fig. 9 - Reverse Recovery Waveform and Definitions

# VS-HFA15TB60S-M3, VS-HFA15TB60-1-M3

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### **ORDERING INFORMATION TABLE**

#### Device code



1 - Vishay Semiconductors product

2 - HEXFRED® family

Electron irradiated

Current rating (15 = 15 A)

5 - Package: TB = TO-220

6 - Voltage rating (60 = 600 V)

 $\overline{7}$  - • S = D<sup>2</sup>PAK (TO-263AB)

- • -1 = TO-262AA

8 - • None = tube (50 pieces)

• L = tape and reel (left oriented, for D2PAK (TO-263AB) package )

• R = tape and reel (right oriented, for D<sup>2</sup>PAK (TO-263AB) package)

9 - -M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

| ORDERING INFORMATION (Example) |               |                         |  |  |  |  |
|--------------------------------|---------------|-------------------------|--|--|--|--|
| PREFERRED P/N                  | BASE QUANTITY | PACKAGING DESCRIPTION   |  |  |  |  |
| VS-HFA15TB60S-M3               | 50            | Antistatic plastic tube |  |  |  |  |
| VS-HFA15TB60SL-M3              | 800           | 13" diameter reel       |  |  |  |  |
| VS-HFA15TB60SR-M3              | 800           | 13" diameter reel       |  |  |  |  |
| VS-HFA15TB60-1-M3              | 50            | Antistatic plastic tube |  |  |  |  |

| LINKS TO RELATED DOCUMENTS |                               |                          |  |  |  |  |
|----------------------------|-------------------------------|--------------------------|--|--|--|--|
| Dimensions                 | D <sup>2</sup> PAK (TO-263AB) | www.vishay.com/doc?96164 |  |  |  |  |
| Differsions                | TO-262AA                      | www.vishay.com/doc?96165 |  |  |  |  |
| Part marking information   | D <sup>2</sup> PAK (TO-263AB) | www.vishay.com/doc?95444 |  |  |  |  |
|                            | TO-262AA                      | www.vishay.com/doc?95443 |  |  |  |  |
| Packaging information      |                               | www.vishay.com/doc?96424 |  |  |  |  |
| SPICE model                |                               | www.vishay.com/doc?95357 |  |  |  |  |



### Vishay Semiconductors

### D<sup>2</sup>PAK

### **DIMENSIONS** in millimeters and inches



| SYMBOL   | MILLIM | ETERS | INC   | HES   | NOTES | SYMBOL   | MILLIM | ETERS | INC   | HES   | NOTES |
|----------|--------|-------|-------|-------|-------|----------|--------|-------|-------|-------|-------|
| STIVIBUL | MIN.   | MAX.  | MIN.  | MAX.  | NOIES | STINIBUL | MIN.   | MAX.  | MIN.  | MAX.  | NOTES |
| Α        | 4.06   | 4.83  | 0.160 | 0.190 |       | D1       | 6.86   | 8.00  | 0.270 | 0.315 | 3     |
| A1       | 0.00   | 0.254 | 0.000 | 0.010 |       | E        | 9.65   | 10.67 | 0.380 | 0.420 | 2, 3  |
| b        | 0.51   | 0.99  | 0.020 | 0.039 |       | E1       | 7.90   | 8.80  | 0.311 | 0.346 | 3     |
| b1       | 0.51   | 0.89  | 0.020 | 0.035 | 4     | е        | 2.54   | BSC   | 0.100 | BSC   |       |
| b2       | 1.14   | 1.78  | 0.045 | 0.070 |       | Н        | 14.61  | 15.88 | 0.575 | 0.625 |       |
| b3       | 1.14   | 1.73  | 0.045 | 0.068 | 4     | L        | 1.78   | 2.79  | 0.070 | 0.110 |       |
| С        | 0.38   | 0.74  | 0.015 | 0.029 |       | L1       | -      | 1.65  | -     | 0.066 | 3     |
| c1       | 0.38   | 0.58  | 0.015 | 0.023 | 4     | L2       | 1.27   | 1.78  | 0.050 | 0.070 |       |
| c2       | 1.14   | 1.65  | 0.045 | 0.065 |       | L3       | 0.25   | BSC   | 0.010 | BSC   |       |
| D        | 8.51   | 9.65  | 0.335 | 0.380 | 2     | L4       | 4.78   | 5.28  | 0.188 | 0.208 |       |

#### Notes

- (1) Dimensioning and tolerancing per ASME Y14.5 M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- (3) Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Datum A and B to be determined at datum plane H
- (6) Controlling dimension: inches
- (7) Outline conforms to JEDEC® outline TO-263AB

Revision: 13-Jul-17 Document Number: 96164

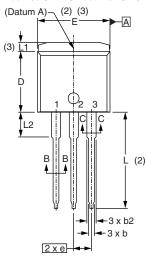


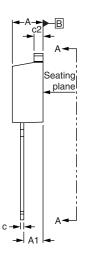
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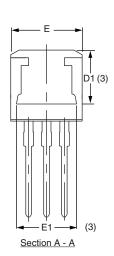
### **TO-262AA**

### **DIMENSIONS** in millimeters and inches

#### Modified JEDEC® outline TO-262







**⊕** 0.010 **M** A**M** B

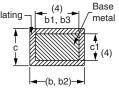
#### Lead assignments



**Diodes** 1. - Anode (two die)/open (one die)

2., 4. - Cathode

3. - Anode



Section B - B and C - C Scale: None

| SYMBOL  | MILLIN  | METERS | INC   | INCHES |       |  |  |
|---------|---------|--------|-------|--------|-------|--|--|
| STWIDUL | MIN.    | MAX.   | MIN.  | MAX.   | NOTES |  |  |
| Α       | 4.06    | 4.83   | 0.160 | 0.190  |       |  |  |
| A1      | 2.03    | 3.02   | 0.080 | 0.119  |       |  |  |
| b       | 0.51    | 0.99   | 0.020 | 0.039  |       |  |  |
| b1      | 0.51    | 0.89   | 0.020 | 0.035  | 4     |  |  |
| b2      | 1.14    | 1.78   | 0.045 | 0.070  |       |  |  |
| b3      | 1.14    | 1.73   | 0.045 | 0.068  | 4     |  |  |
| С       | 0.38    | 0.74   | 0.015 | 0.029  |       |  |  |
| c1      | 0.38    | 0.58   | 0.015 | 0.023  | 4     |  |  |
| c2      | c2 1.14 | 1.65   | 0.045 | 0.065  |       |  |  |
| D       | 8.51    | 9.65   | 0.335 | 0.380  | 2     |  |  |
| D1      | 6.86    | 8.00   | 0.270 | 0.315  | 3     |  |  |
| E       | 9.65    | 10.67  | 0.380 | 0.420  | 2, 3  |  |  |
| E1      | 7.90    | 8.80   | 0.311 | 0.346  | 3     |  |  |
| е       | 2.54    | BSC    | 0.10  | 0 BSC  |       |  |  |
| L       | 13.46   | 14.10  | 0.530 | 0.555  |       |  |  |
| L1      | -       | 1.65   | -     | 0.065  | 3     |  |  |
| L2      | 3.56    | 3.71   | 0.140 | 0.146  |       |  |  |

#### **Notes**

(4) Dimension b1 and c1 apply to base metal only

Controlling dimension: inches

<sup>(1)</sup> Dimensioning and tolerancing as per ASME Y14.5M-1994
(2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body

Thermal pad contour optional within dimension E, L1, D1 and E1

Outline conform to JEDEC® TO-262 except A1 (max.), b (min., max.), b1 (min.), b2 (max.), c (min.), c1(min.), c2 (max.), D (min.), E (max.), L1 (max.), L2 (min., max.)



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